

Zibo Seno Electronic Engineering Co., Ltd.



BZX584B2V4G-BZX584B75G



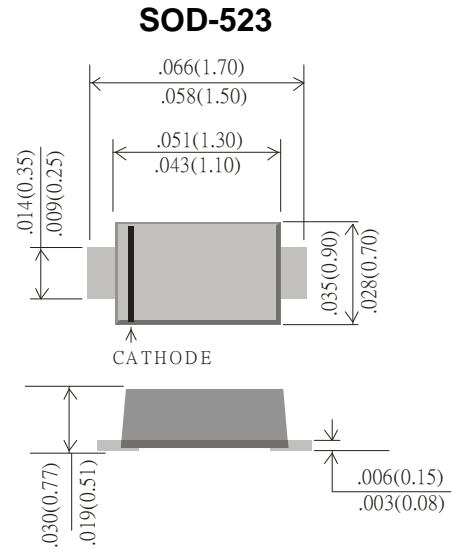
100mW SURFACE MOUNT ZENER DIODE

Features

- Planar Die Construction
- Sealed Glass Case
- Ideally Suited for Automated Insertion
- 2.4V - 43V Nominal Zener Voltages

Mechanical Data

- Case: SOD-523, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Approx. Weight: 0.005 grams
- **Lead Free: For RoHS / Lead Free Version**



Dimensions in inch & mm

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1)	P _d	100	mW
Forward Voltage @ I _F = 10mA	V _F	0.9	V
Thermal Resistance, Junction to Ambient Air (Note 2)	R _{θJA}	625	K/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

NOTE: 1.DEVICE MOUNTED ON CERAMIC PCB:7.6mm x 9.4mm x 0.87mm WITH PAD AREAS 25mm².
 2.TESTED WITH PULSES,T_p ≤ 1.0ms.
 3. f = 1KHZ

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Electrical Characteristics @ T_A = 25°C unless otherwise specified

Part Number	Nominal Zener Voltage			Max. Zener Impedance				Max Reverse Leakage Current	
	V _Z @ I _{ZT}			Z _{ZT} @ I _{ZT}		Z _{ZK} @ I _{ZK}		I _R @ V _R	
	Nom. V	Min. V	Max. V	Ω	mA	Ω	mA	μA	V
BZX584B2V4G	2.4	2.352	2.448	100	5.0	600	1.00	120	1.0
BZX584B2V7G	2.7	2.646	2.754	110	5.0	600	1.00	120	1.0
BZX584B3V0G	3.0	2.940	3.060	120	5.0	600	1.00	50	1.0
BZX584B3V3G	3.3	3.234	3.366	130	5.0	600	1.00	20	1.0
BZX584B3V6G	3.6	3.528	3.672	130	5.0	600	1.00	10	1.0
BZX584B3V9G	3.9	3.822	3.978	130	5.0	600	1.00	5.0	1.0
BZX584B4V3G	4.3	4.214	4.386	130	5.0	600	1.00	5.0	1.0
BZX584B4V7G	4.7	4.606	4.794	130	5.0	500	1.00	2.0	1.0
BZX584B5V1G	5.1	4.998	5.202	130	5.0	480	1.00	2.0	1.5
BZX584B5V6G	5.6	5.488	5.712	80	5.0	400	1.00	1.0	2.5
BZX584B6V2G	6.2	6.076	6.324	50	5.0	150	1.00	1.0	3.0
BZX584B6V8G	6.8	6.664	6.936	30	5.0	80	1.00	0.5	3.5
BZX584B7V5G	7.5	7.350	7.650	30	5.0	80	1.00	0.5	4.0
BZX584B8V2G	8.2	8.036	8.364	30	5.0	80	1.00	0.5	5.0
BZX584B9V1G	9.1	8.918	9.282	30	5.0	100	1.00	0.5	6.0
BZX584B10G	10	9.800	10.200	30	5.0	150	1.00	0.1	7.0
BZX584B11G	11	10.780	11.220	30	5.0	150	1.00	0.1	8.0
BZX584B12G	12	11.760	12.240	35	5.0	150	1.00	0.1	9.0
BZX584B13G	13	12.740	13.260	35	5.0	170	1.00	0.1	10.0
BZX584B15G	15	14.700	15.300	40	5.0	200	1.00	0.1	11.0
BZX584B16G	16	15.680	16.320	40	5.0	200	1.00	0.1	12.0
BZX584B18G	18	17.640	18.360	45	5.0	225	1.00	0.1	13.0
BZX584B20G	20	19.600	20.400	50	5.0	225	1.00	0.1	15.0
BZX584B22G	22	21.560	22.440	55	5.0	250	1.00	0.1	17.0
BZX584B24G	24	23.520	24.480	60	5.0	250	1.00	0.1	19.0
BZX584B27G	27	26.460	27.540	70	2.0	300	0.50	0.1	21.0
BZX584B30G	30	29.400	30.600	80	2.0	300	0.50	0.1	23.0
BZX584B33G	33	32.340	33.660	80	2.0	325	0.50	0.1	25.0
BZX584B36G	36	35.280	36.720	90	2.0	350	0.50	0.1	27.0
BZX584B39G	39	38.220	39.780	100	2.0	350	0.50	2.0	30.0
BZX584B43G	43.0	42.140	43.860	130	2.0	500	0.50	2.0	33.0
BZX584B47G	47.0	46.060	47.940	150	2.0	500	0.50	2.0	36.0
BZX584B51G	51.0	49.980	52.020	180	2.0	500	0.50	1.0	39.0
BZX584B56G	56.0	54.880	57.120	180	2.0	500	0.50	1.0	43.0
BZX584B62G	62.0	60.760	63.240	200	2.0	500	0.50	0.2	47.0
BZX584B68G	68.0	66.640	69.360	250	2.0	500	0.50	0.2	52.0
BZX584B75G	75.0	73.500	76.500	300	2.0	500	0.50	0.2	57.0

Characteristics ($T_j=25^\circ\text{C}$ unless otherwise specified)

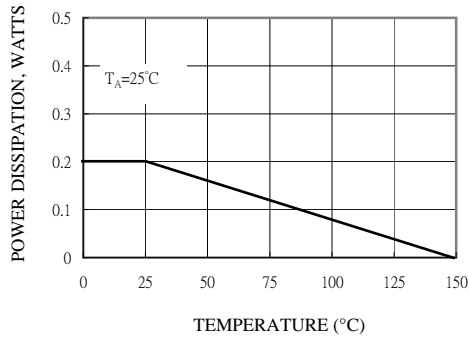


Fig.1- STEADY STATE POWER DERATING

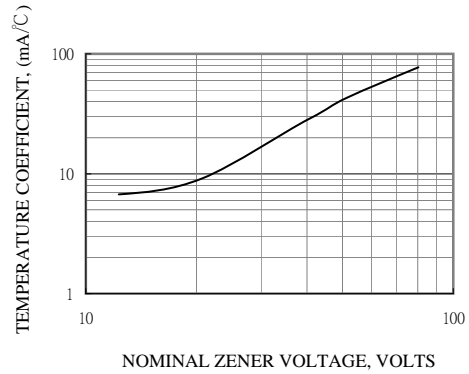


Fig.2- TEMPERATURE COEFFICIENTS

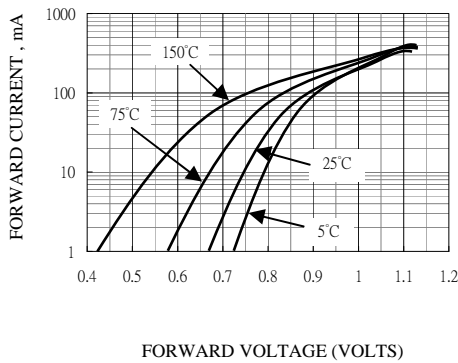


Fig.3- TYPICAL FORWARD VOLTAGE

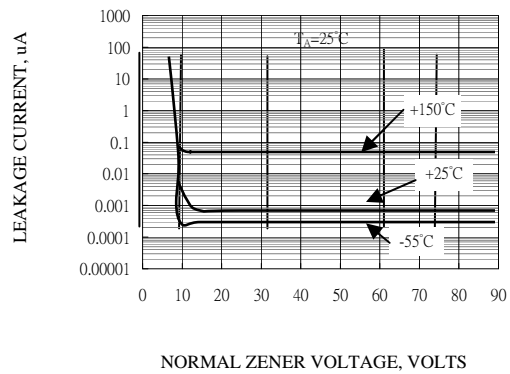


Fig.4- TYPICAL LEAKAGE CURRENT